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# SOT-89 CB3401U



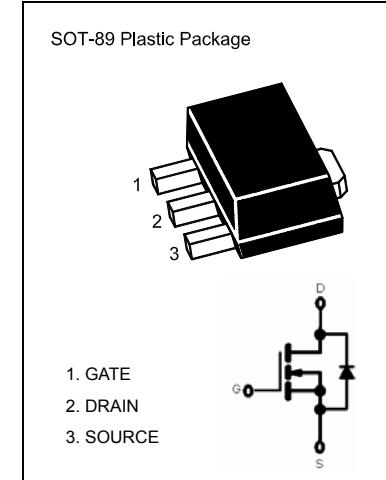
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## SOT-89 Plastic-Encapsulate MOSFETS

P-Channel Enhancement Mode Field Effect Transistor

### FEATURE

- High dense cell design for extremely low  $R_{DS(ON)}$ .
- Exceptional on-resistance and maximum DC current capability



MARKING: 3401

Maximum ratings (  $T_a=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	-4.2	A
Power Dissipation	$P_D$	350	mW
Thermal Resistance from Junction to Ambient (t<5s)	$R_{\theta JA}$	357	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~+150	°C



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### Electrical characteristics ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off characteristics</b>						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-30			V
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}} = -24\text{V}, V_{\text{GS}} = 0\text{V}$			-1	$\mu\text{A}$
Gate-source leakage current	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 12\text{V}, V_{\text{DS}} = 0\text{V}$			$\pm 100$	nA
<b>On characteristics</b>						
Drain-source on-resistance (note 1)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, I_D = -4.2\text{A}$			65	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}, I_D = -4\text{A}$			75	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}, I_D = -1\text{A}$			90	$\text{m}\Omega$
Forward transconductance (note 1)	$g_{\text{FS}}$	$V_{\text{DS}} = -5\text{V}, I_D = -5\text{A}$	7			S
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-0.7		-1.3	V
<b>Dynamic characteristics</b> (note 2)						
Input capacitance	$C_{\text{iss}}$	$V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		954		pF
Output capacitance	$C_{\text{oss}}$			115		pF
Reverse transfer capacitance	$C_{\text{rss}}$			77		pF
<b>Switching characteristics</b> (note 2)						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, V_{\text{DS}} = -15\text{V}, R_L = 3.6\Omega, R_{\text{GEN}} = 6\Omega$			6.3	ns
Turn-on rise time	$t_r$				3.2	ns
Turn-off delay time	$t_{\text{d}(\text{off})}$				38.2	ns
Turn-off fall Time	$t_f$				12	ns
<b>Drain-source diode characteristics and maximum ratings</b>						
Diode forward voltage (note 1)	$V_{\text{SD}}$	$I_S = -1\text{A}, V_{\text{GS}} = 0\text{V}$			-1	V

#### Note :

1. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
2. These parameters have no way to verify.



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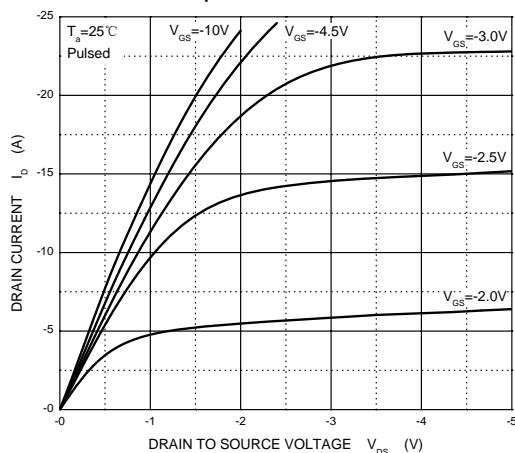


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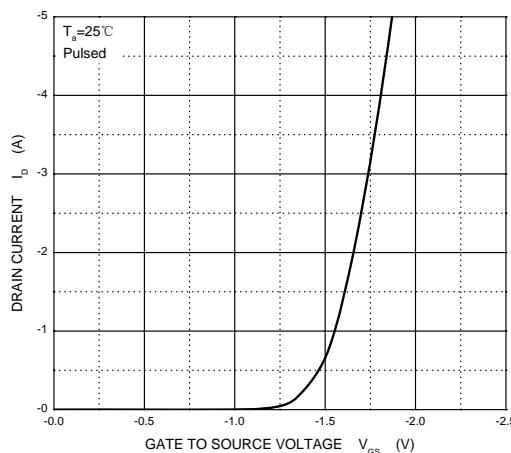
## Typical Characteristics

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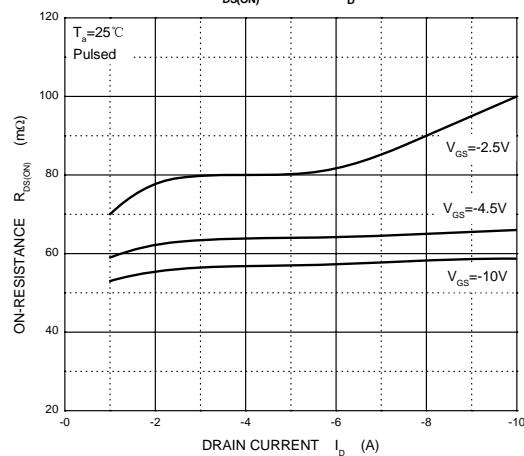
Output Characteristics



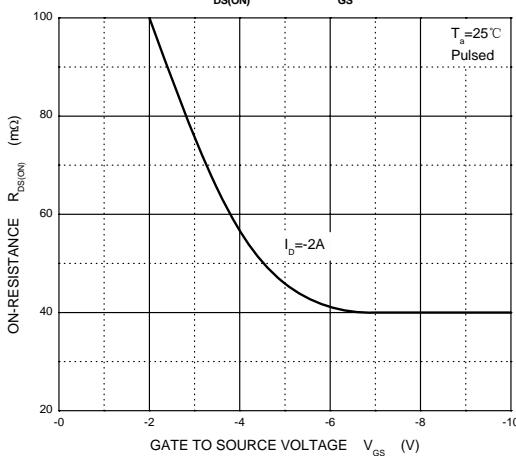
Transfer Characteristics



$R_{DS(ON)}$  —  $I_D$



$R_{DS(ON)}$  —  $V_{GS}$



$I_S$  —  $V_{SD}$

